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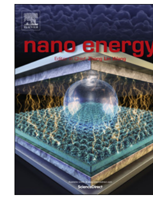


Communication

# Concurrent improvement in optical and electrical characteristics by using inverted pyramidal array structures toward efficient Si heterojunction solar cells

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The Si heterojunction (SHJ) solar cell is presently the most popular design in the crystalline Si (*c*-Si) photovoltaics due to the high open-circuit voltages ($V_{OC}$). Photon management by surface structuring techniques to control the light entering the devices is critical for boosting cell efficiency although it usually comes with the $V_{OC}$ loss caused by severe surface recombination. For the first time, the periodic inverted pyramid (IP) structure fabricated by photolithography and anisotropic etching processes was employed for SHJ solar cells, demonstrating concurrent improvement in optical and electrical characteristics (i.e., short-circuit current density ($J_{SC}$) and $V_{OC}$). Periodic IP structures show superior light-harvesting properties as most of the incident rays bounce three times on the walls of the IPs but only twice between conventional random upright pyramids (UPs). The high minority carrier lifetime of the IP structures after *a*-Si:H passivation results in an enhanced $V_{OC}$ by 28 mV, showing improved carrier collection efficiency due to the superior passivation of the IP structure over the random UP structures. The superior antireflective (AR) ability and passivation results demonstrate that the IP structure has the potential to replace conventional UP structures to further boost the efficiency in solar cell applications.


## 1. Introduction

Energy harvesting in photovoltaic (PV) devices has become critical with continuous improvements in cell design for boosting cell efficiency. A lot of research efforts have focused on photon management to precisely control the light at the active layer to efficiently generate photocarriers. However, most of light-trapping schemes by employing surface structuring techniques usually accompany electrical losses (*e.g.*, carrier recombination by surface states or contact losses) [1–3]. The expected boosted short-circuit current density ($J_{SC}$) would be partially compromised by poor open-circuit voltages ($V_{OC}$) and fill factors (*FF*). Therefore, no matter what light-trapping techniques are applied on PV devices, the electrical properties need to be considered. How to optimize the trade-off between optical gain and electrical loss or even concurrently improve both optical and electrical characteristics become the most important issues for putting photon management into practice.

Heterojunction structure has been widely studied for different types of solar cells [4–7]. Generally, great solar cells must generate maximum photocarriers by broadband absorption at active region, but also assure these photo-generated carriers can be efficiently collected with minimal recombination when they travel to the terminals of the device. High recombination increases the diode saturation current, reducing the $V_{OC}$. By insertion of a film with wide bandgap, the carrier recombination can be efficiently reduced due to a large band offset at the heterojunction interface, leading to a higher $V_{OC}$ [8]. Recently, the amorphous/crystalline Si (*a*-Si/*c*-Si) heterojunction solar cell structure currently is the most popular design in *c*-Si PV industries. It combines the advantages of *c*-Si solar cells with the excellent absorption and long minority carrier lifetimes and the advantage of hydrogenated *a*-Si (*a*-Si:H) with passivation characteristics [9]. The most impressive feature of this structure is its high $V_{OC}$ which occurs due to the significant passivation effect of *a*-Si:H. Not only can the surface state density of *c*-Si be reduced, but the wide bandgap of *a*-Si:H generates a large band offset at the *a*-Si:H/*c*-Si interface, minimizing the carrier recombination loss [10]. In 2014, a world-record high efficiency among all kinds of Si-based solar cells of 25.6% was obtained with a Si heterojunction (SHJ) combined with an interdigitated back contact design [11]. According to loss analysis, the optical loss was 60–70% of the total loss [12]. By using an interdigitated back contact design, the optical loss from the metal grid electrodes and absorption of ITO on the front side can be avoided, leading to an improvement in the $J_{SC}$ of 2.3 mA/cm$^2$.

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$J_{SC}$ enhancement *via* light-trapping structures is another choice to further improve the performance of SHJ solar cells. However, it is critical to design antireflective (AR) structures for SHJ solar cells. In addition to exceptional AR ability, to avoid sacrificing the high $V_{OC}$, it is important to well passivate the surface of solar cells. In the SHJ case, cells must be able to be well passivated by intrinsic *a*-Si:H films as thin as 5 nm. But it is difficult to employ high aspect-ratio light-trapping structures such as nanowires in SHJ solar cells because of the non-uniform coverage of *a*-Si:H and subsequent layers, which results in the degradation of the PV performance [13–18]. A random upright pyramid (UP) structure fabricated by anisotropic wet chemical etching is the most commonly used for *c*-Si-based solar cells [19–22]. However, the various sizes of random UPs with sharp pyramidal peaks do not appear to be good enough for *a*-Si:H passivation. A chemical polish treatment for structured surfaces has been developed to improve the passivation effect, but there is a corresponding decrease in the light-trapping ability [14,18,23,24]. Inverted pyramid (IP) structures, which show better light confinement than UP structures, might be a good candidate for SHJ solar cells [25–28]. Moreover, since the morphologies of IP structures are relatively uniform, without sharp peaks, they have the potential to offer better passivation results, resulting in higher $V_{OC}$.

Many researches only discussed the AR properties of IP structures, neglecting to look into the electrical properties after applying on practical devices. A comparison of IP structures with conventional random UP structures in SHJ devices has not yet been made. Thus, in this work, SHJ solar cells with polished, random UP and different sizes of IP surfaces are compared. The influences on the AR ability and the passivation effect of different geometric structures are investigated. It is found that the average total reflectance ($R_{total}$) of SHJ cells can be suppressed to less than 4.5% over a wide spectral range from 400 to 1000 nm by using the IP with 10 μm periodicity. There is a big enhancement in the $J_{SC}$ and power conversion efficiency (CE) for IP textured SHJ solar cells (35.3 mA/cm$^2$ and 14.6%) compared to the random UP textured SHJ solar cells (34.2 mA/cm$^2$ and 12.7%). It is noteworthy that the $V_{OC}$ of the IP textured SHJ solar cells is 28 mV higher than that of the random UPs, indicating the superior passivation of the IP structure over the random UP textured structures. We demonstrate that the IP structures with their superior AR ability and passivation results have the potential to replace the random UP structures, to further boost the efficiency in SHJ solar cell applications. Finally, the SHJ solar cell with the optimized IP structure exhibits a CE of 14.6% with $J_{SC}$ of 35.3 mA/cm$^2$, $V_{OC}$ of 605.4 mV, and *FF* of 68.4%.

## 2. Experimental section

The SHJ solar cells were fabricated using the process illustrated in the flowchart in Fig. S1 in Supporting Information. Random UPs and periodic IPs were fabricated on 4-in. n-type monocrystalline Si Czochralski (001) wafers with a thickness of 200 μm. The random UP structures were obtained by immersing the Si substrates in a potassium hydroxide solution (KOH:IPA:$H_2O$ = 1:1:17) for 20 min at 85 °C. Rectangular arrays with different periodicities were patterned by photolithography using the IP fabrication process. After this, a 30-nm-thick $SiO_2$ layer was deposited as an etching mask. After the lift-off process, the substrates with patterned $SiO_2$ layers were immersed in a potassium hydroxide solution (KOH:IPA:$H_2O$ = 1:1:17) at 85 °C. After $SiO_2$ removal by HF, IP structures with different periodicities were obtained. Subsequently, all patterned substrates were cleaned by the standard RCA process followed by dipping in 1% HF. To fabricate SHJ solar cells, an intrinsic buffer (10 nm)/p-type-doped *a*-Si:H layer (6 nm) were deposited on the front, and an intrinsic buffer (10 nm)/n-type-doped *a*-Si:H layer (10 nm) were deposited on the back by plasma-enhanced chemical vapor deposition (PECVD) at 150 °C. A 92-nm-thick ITO layer was deposited by sputtering on the both sides as a transparent conducting layer. After deposition of the ITO films, the cells were annealed at 210 °C in air for 30 min. Finally, Ag grids were deposited on the both sides by e-beam evaporation.

Morphological studies were carried out using JEOL JSM-6500 field emission SEM. Reflectance measurements were performed by a JASCO V-670 UV–vis spectrometer equipped with an integral sphere. The minority carrier lifetime measurement was analyzed using the quasi-steady-state photoconductance technique (QSSPC) on a Sinton WCT120. The PV performance of the current density-voltage (*J*–*V*) characteristics was monitored under illumination by an air mass (AM) 1.5G solar simulator at 100 mW/cm$^2$ with a Keithley 2400 source meter. External quantum efficiency (*EQE*) measurements were performed by coupling a Halogen lamp to a monochromator.

## 3. Results and discussion

Fig. 1a shows the structure of a complete SHJ solar cell. Fig. 1b–d illustrates three kinds of Si surfaces for comparison: polished, random UP, and periodic IP surfaces. The SEM images of the random UP and the periodic IP structures are shown in Fig. 1e and f. Conventional random UPs ranging from 7 to 14 μm in width were fabricated by immersing as-cut Si substrates in an anisotropic etching solution. Some pyramids less than 1 μm in width or half pyramids were also generated between big pyramids (Fig. 1e). It is difficult to obtain a surface with the same size of UPs by only using wet etching, even changing concentration of etching solution, time, or temperature [29]. Pyramids with an angle of 54.7° to the wafer surface formed at a much higher etching rate in the [100] direction than that in the [111] direction due to the higher atomic density in the (111) plane than that in the (100) plane [30]. Large areas of periodic IP structures with different periodicities were obtained by using photolithography technique combined with the anisotropic etching process. Fig. S2a–S2c in Supporting Information show the SEM images of the IP structures with periodicities of 6, 10, and 14 μm, respectively. The sizes of the IPs are controlled by photolithography and etching time. The ridge width of the IP structures is controlled in the range of 1–1.5 μm.

To investigate the light-harvesting abilities of the IP structures, the spectral $R_{total}$ was measured for comparison with substrates with polished and random UP surfaces. Fig. S3 in Supporting Information shows the $R_{total}$ of IP structures with different periodicities to first optimize the IP structures. The IP structure with a 10-μm periodicity exhibits the lowest reflectance over the wavelength range from 300 to 1100 nm. Optical and electrical properties of IP with optimized 10-μm periodicity would be compared with polished and random UP surfaces in the following study. In contrast to polished and UP surfaces, the IP surface reduces the reflectance over the broadband regions and exhibits reduced average $R_{total}$ from 41.2% (polished surface) and 19.2% (random UP surface) to 15.3% (Fig. 2a). The IP surface shows lower $R_{total}$ than the random UP surface because of the superior light–trapping ability of the periodic IP structures. The incident rays bounce multiple times off the pyramidal structures with incident light absorbed during every bounce. The large difference in the size of the UPs is disadvantageous to confining the light within the structures. Moreover, from the simulation, it can be seen that most of the incident rays bounce three times on the walls of the IPs but only twice between the UPs. The increased number of bounces of reflected light in the IPs increases the probability of light absorption [26,27,31]. Furthermore, the light scattered by the structures enters the substrates at oblique angles, increasing the length of the optical path, which is important especially in solar cell application.



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